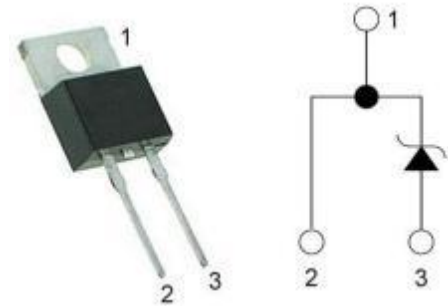


Product Summary

$V_R = 650\text{ V}$
 $I_F = 10\text{ A (}T_C=150^\circ\text{C)}$
 $Q_C = 23\text{ nC (}V_R=400\text{ V)}$



TO-220-2

Features

- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

Applications

- Motor Drives
- Solar
- AC/DC Converters
- DC/DC Converters
- Uninterruptable Power Supplies

Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | Value | Unit |
|---------------------------------------|-----------|--|------------|------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | | 650 | V |
| Peak Reverse Surge Voltage | V_{RSM} | | 650 | V |
| DC Blocking Voltage | V_R | | 650 | V |
| Continuous Forward Current | I_F | $T_C=25^\circ\text{C}$ | 32 | A |
| | | $T_C=135^\circ\text{C}$ | 14 | |
| | | $T_C=150^\circ\text{C}$ | 10 | |
| Non repetitive Forward Surge Current | I_{FSM} | $T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$, Half Sine Pulse | 65 | A |
| | | $T_C = 150^\circ\text{C}$, $t_p=10\text{ ms}$, Half Sine Pulse | 55 | |
| | | $T_C = 25^\circ\text{C}$, $t_p=10\text{ }\mu\text{s}$, Square | 520 | |
| Repetitive peak Forward Surge Current | I_{FRM} | $T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$, Freq = 0.1Hz, 100 cycles, Half Sine Pulse | 55 | A |
| | | $T_C = 150^\circ\text{C}$, $t_p=10\text{ ms}$, Freq = 0.1Hz, 100 cycles, Half Sine Pulse | 45 | |
| Total power dissipation | P_D | $T_C=25^\circ\text{C}$ | 94 | W |
| Operating Junction Temperature | T_J | | -55 to 175 | $^\circ\text{C}$ |
| Storage Temperature | T_{STG} | | -55 to 175 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|-------------------------|----------|--|-----|------|-----|---------|
| DC Blocking Voltage | V_{DC} | $I_R = 250\mu A, T_J = 25^\circ C$ | 650 | | | V |
| Forward Voltage | V_F | $I_F = 10A, T_J = 25^\circ C$ | | 1.45 | 1.8 | V |
| | | $I_F = 10A, T_J = 125^\circ C$ | | 1.6 | | |
| | | $I_F = 10A, T_J = 175^\circ C$ | | 1.7 | | V |
| Reverse Current | I_R | $V_R = 650V, T_J = 25^\circ C$ | | 12 | 80 | μA |
| | | $V_R = 650V, T_J = 125^\circ C$ | | 68 | | μA |
| | | $V_R = 650V, T_J = 175^\circ C$ | | 190 | | μA |
| Total Capacitive Charge | Q_C | $V_R = 400V$ $T_J = 25^\circ C$ | | 23 | | nC |
| Total Capacitance | C | $V_R = 1V, T_J = 25^\circ C,$ Freq = 1MHz | | 380 | | pF |
| | | $V_R = 200V, T_J = 25^\circ C,$ Freq = 1MHz | | 48 | | |
| | | $V_R = 400V, T_J = 25^\circ C,$ Freq = 1MHz | | 31 | | |

Note: This is a majority carrier diode, so there is no reverse recovery charge

Thermal Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|--------------------|---------------|---------------|-----|-----|-----|--------------|
| Thermal Resistance | $R_{th(j-c)}$ | junction-case | | 1.6 | | $^\circ C/W$ |

Typical Electrical Curves

Figure 1. Forward Characteristics

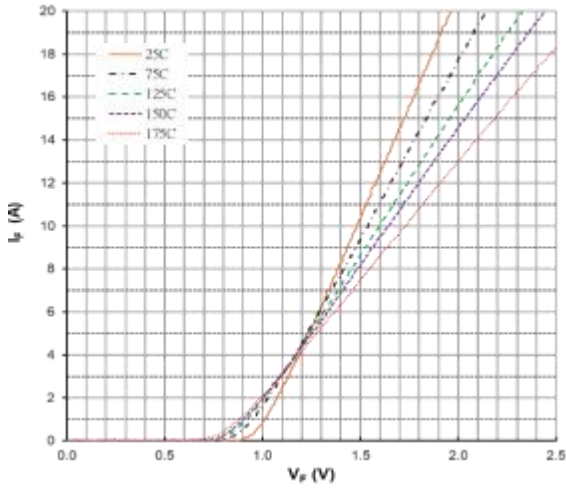


Figure 2. Forward Characteristics

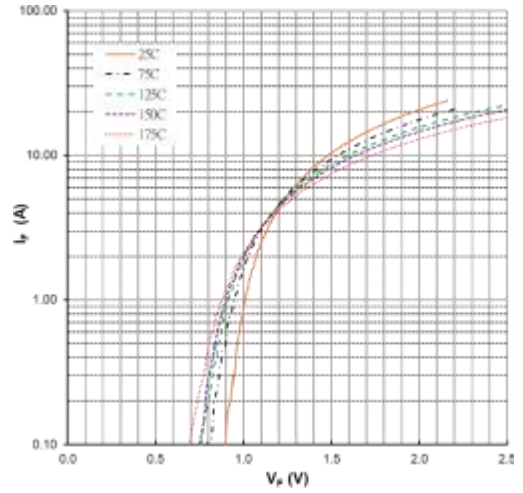


Figure 3. Reverse Characteristics

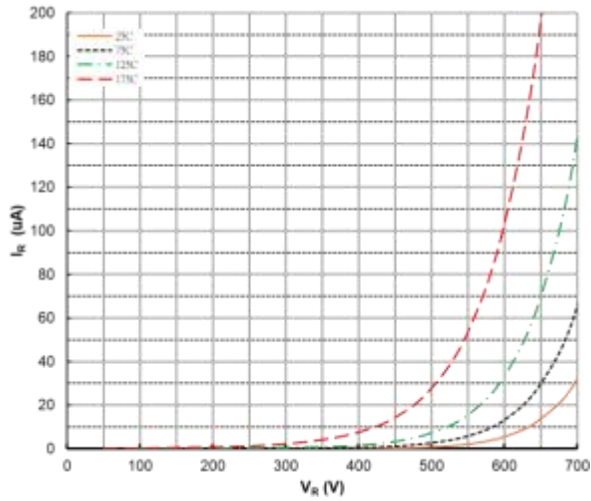


Figure 4. Power Derating

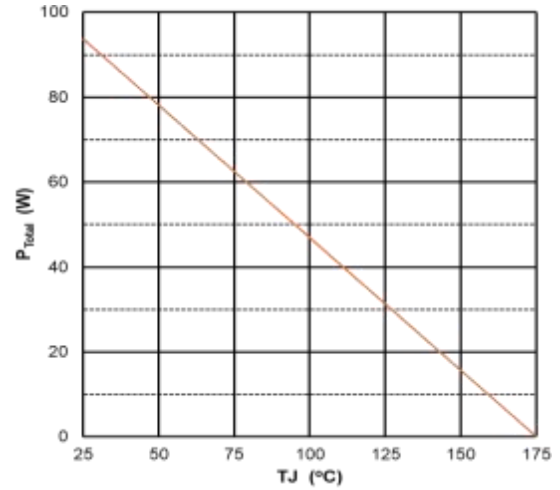


Figure 5. Capacitance vs Reverse Voltage

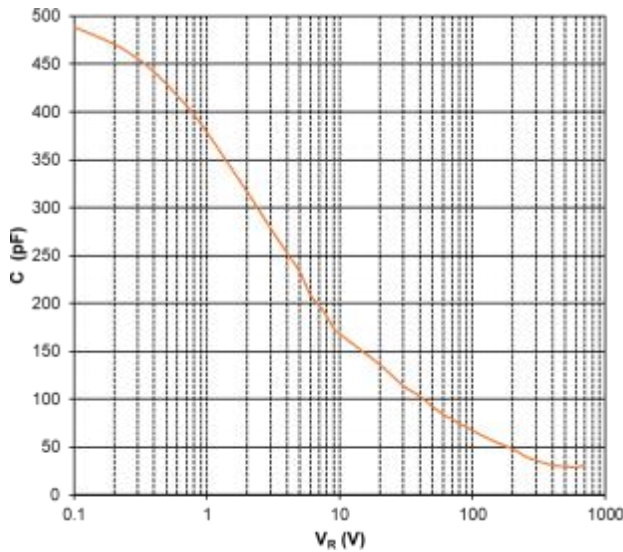
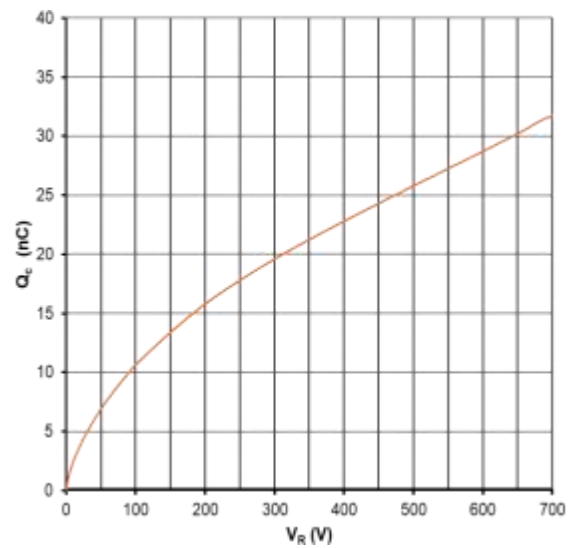
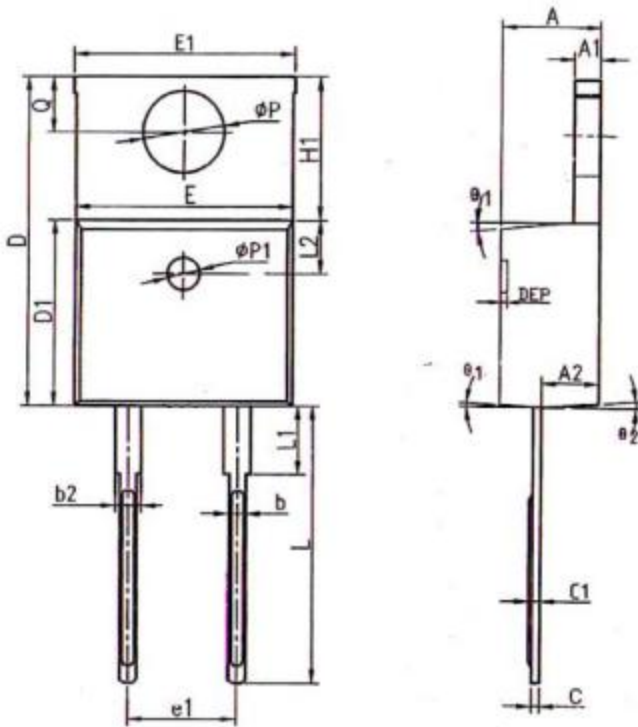


Figure 6. Recovery Charge vs Reverse Voltage



Package Dimensions

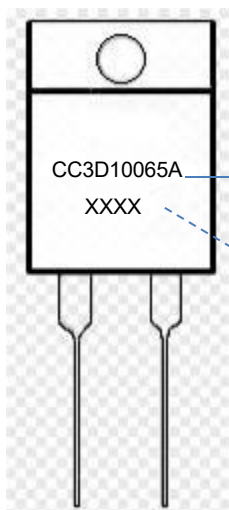
(TO-220-2 Package)



COMMON DIMENSIONS

| SYMBOL | MM | | | INCH | | |
|------------|----------|-------|-------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 4.40 | 4.57 | 4.70 | 0.173 | 0.180 | 0.185 |
| A1 | 1.22 | 1.27 | 1.32 | 0.048 | 0.050 | 0.052 |
| A2 | 2.59 | 2.69 | 2.79 | 0.102 | 0.106 | 0.110 |
| b | 0.77 | 0.813 | 0.90 | 0.030 | 0.032 | 0.035 |
| b2 | 1.20 | 1.27 | 1.36 | 0.047 | 0.050 | 0.054 |
| c | 0.34 | 0.381 | 0.47 | 0.013 | 0.015 | 0.019 |
| c1 | 0.40 | 0.559 | 0.60 | 0.016 | 0.022 | 0.024 |
| D | 14.70 | 15.00 | 15.30 | 0.579 | 0.591 | 0.602 |
| D1 | 8.60 | 8.70 | 8.80 | 0.339 | 0.343 | 0.346 |
| E | 10.06 | 10.16 | 10.26 | 0.396 | 0.400 | 0.404 |
| E1 | 10.10 | 10.25 | 10.35 | 0.398 | 0.404 | 0.407 |
| E2 | 10.00 | 10.10 | 10.20 | 0.394 | 0.398 | 0.402 |
| e | 2.54 BSC | | | 0.100 BSC | | |
| e1 | 5.08 BSC | | | 0.200 BSC | | |
| H1 | 6.10 | 6.30 | 6.50 | 0.240 | 0.248 | 0.256 |
| L | 13.20 | 13.40 | 13.50 | 0.520 | 0.528 | 0.531 |
| L1 | - | 3.75 | 4.00 | - | 0.148 | 0.157 |
| L2 | 2.50 REF | | | 0.098 REF | | |
| ϕP | 3.76 | 3.84 | 3.88 | 0.148 | 0.151 | 0.153 |
| Q | 2.60 | 2.743 | 2.90 | 0.102 | 0.108 | 0.114 |
| θ_1 | 5° | 7° | 9° | 5° | 7° | 9° |
| θ_2 | 1° | 3° | 5° | 1° | 3° | 5° |
| $\phi P1$ | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| DEP | 0.05 | 0.10 | 0.20 | 0.002 | 0.004 | 0.008 |

| Part Number | Package | Packing | Marking | M.O.Q |
|-------------|----------|--------------|------------|-------|
| CC3D10065A | TO-220-2 | 50pcs / Tube | CC3D10065A | 500 |



CC3: GWBG SiC Diode; D: Single diode; 10: 10A current;
065: 650V voltage; A: TO-220-2

4-6 digits: Traceable code